

IRFB16N50KPbF

Applications

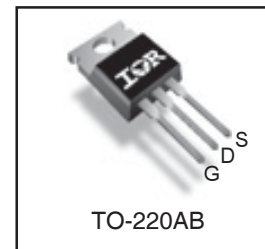
- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits
- Lead-Free

HEXFET® Power MOSFET

V_{DSS}	$R_{DS(on)}$ typ.	I_D
500V	285mΩ	17A

Benefits

- Low Gate Charge Qg results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Low $R_{DS(on)}$



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, VGS @ 10V	17	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, VGS @ 10V	11	
I_{DM}	Pulsed Drain Current ①	68	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	280	W
	Linear Derating Factor	2.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	11	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	310	mJ
I_{AR}	Avalanche Current ①	—	17	A
E_{AR}	Repetitive Avalanche Energy ①	—	28	mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.44	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

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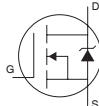
Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.58	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	285	350	mΩ	$V_{GS} = 10V, I_D = 10A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	50	μA	$V_{DS} = 500V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 400V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	5.7	—	—	S	$V_{DS} = 50V, I_D = 10A$
Q_g	Total Gate Charge	—	60	89	nC	$I_D = 17A$
Q_{gs}	Gate-to-Source Charge	—	18	27		$V_{DS} = 400V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	28	43		$V_{GS} = 10V$ ④
$t_{d(on)}$	Turn-On Delay Time	—	20	—	ns	$V_{DD} = 250V$
t_r	Rise Time	—	77	—		$I_D = 17A$
$t_{d(off)}$	Turn-Off Delay Time	—	38	—		$R_G = 8.8\Omega$
t_f	Fall Time	—	30	—		$V_{GS} = 10V$ ④
C_{iss}	Input Capacitance	—	2210	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	240	—		$V_{DS} = 25V$
C_{riss}	Reverse Transfer Capacitance	—	26	—		$f = 1.0MHz$
C_{oss}	Output Capacitance	—	2620	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	63	—		$V_{GS} = 0V, V_{DS} = 400V, f = 1.0MHz$
$C_{oss\ eff.}$	Effective Output Capacitance	—	120	—		$V_{GS} = 0V, V_{DS} = 0V\ to\ 400V$ ③

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	17	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①⑥	—	—	68	A	
V_{SD}	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}, I_S = 17A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	490	730	ns	$T_J = 25^\circ\text{C}, I_F = 17A$
Q_{rr}	Reverse Recovery Charge	—	5710	8560	nC	$di/dt = 100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 2.2mH$, $R_G = 25\Omega$, $I_{AS} = 17A$.

- ③ $I_{SD} \leq 17A$, $di/dt \leq 500A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$.
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

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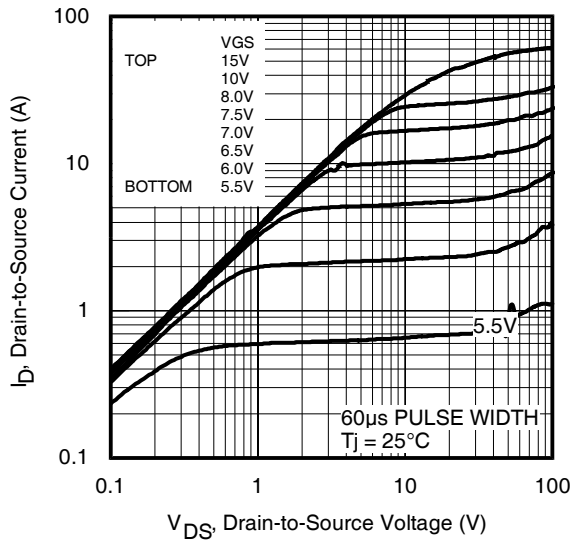


Fig 1. Typical Output Characteristics

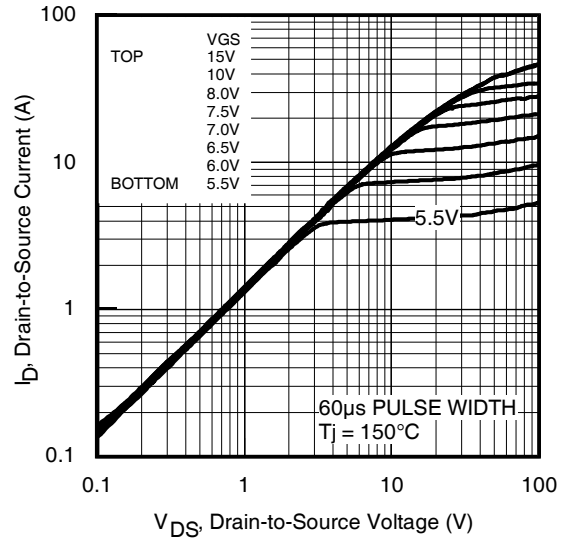


Fig 2. Typical Output Characteristics

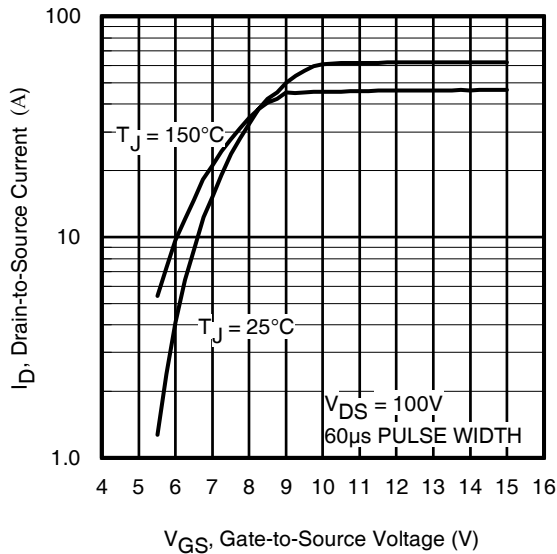


Fig 3. Typical Transfer Characteristics

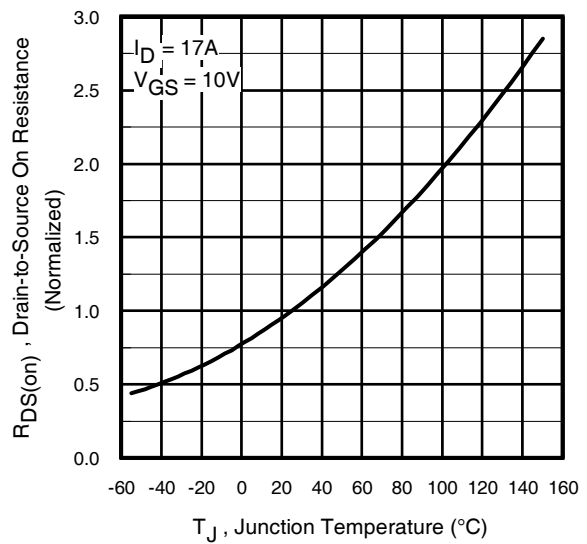


Fig 4. Normalized On-Resistance vs. Temperature

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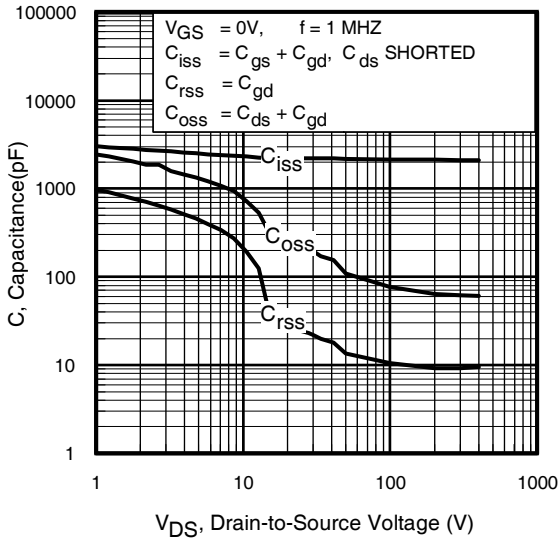


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

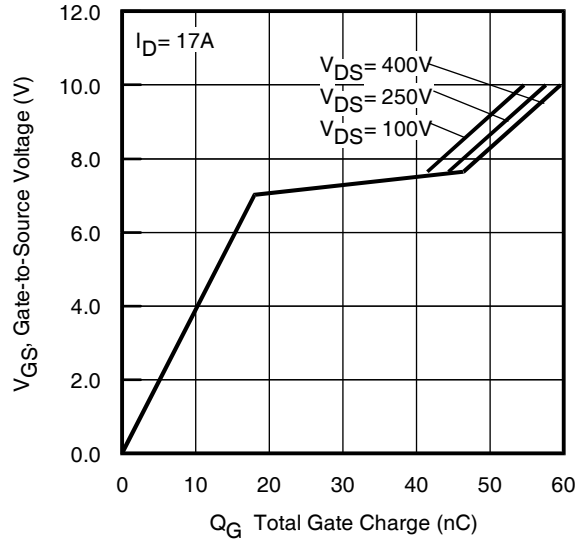


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

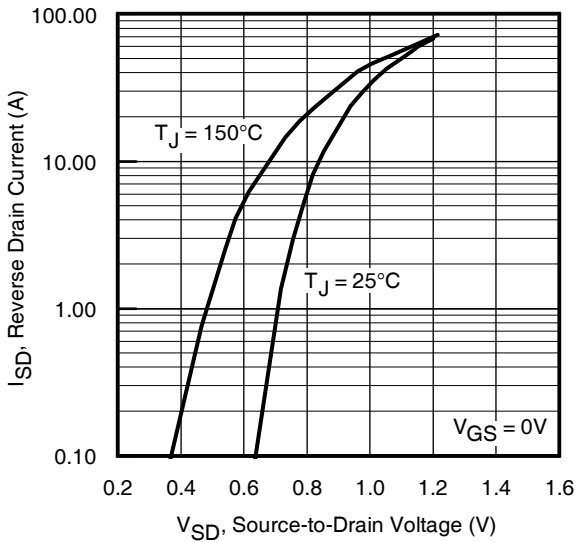


Fig 7. Typical Source-Drain Diode Forward Voltage

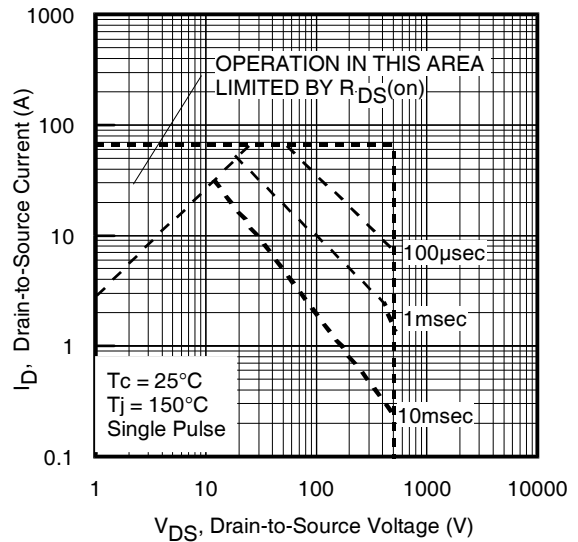


Fig 8. Maximum Safe Operating Area

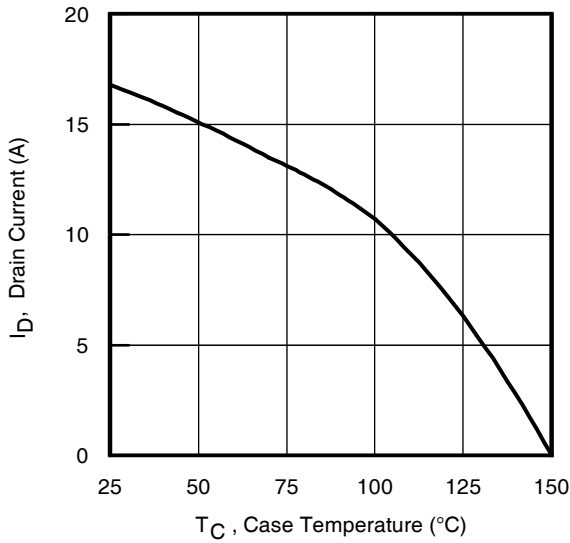


Fig 9. Maximum Drain Current vs. Case Temperature

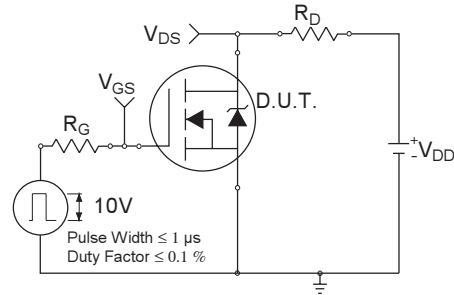


Fig 10a. Switching Time Test Circuit

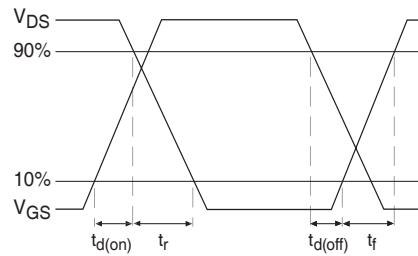


Fig 10b. Switching Time Waveforms

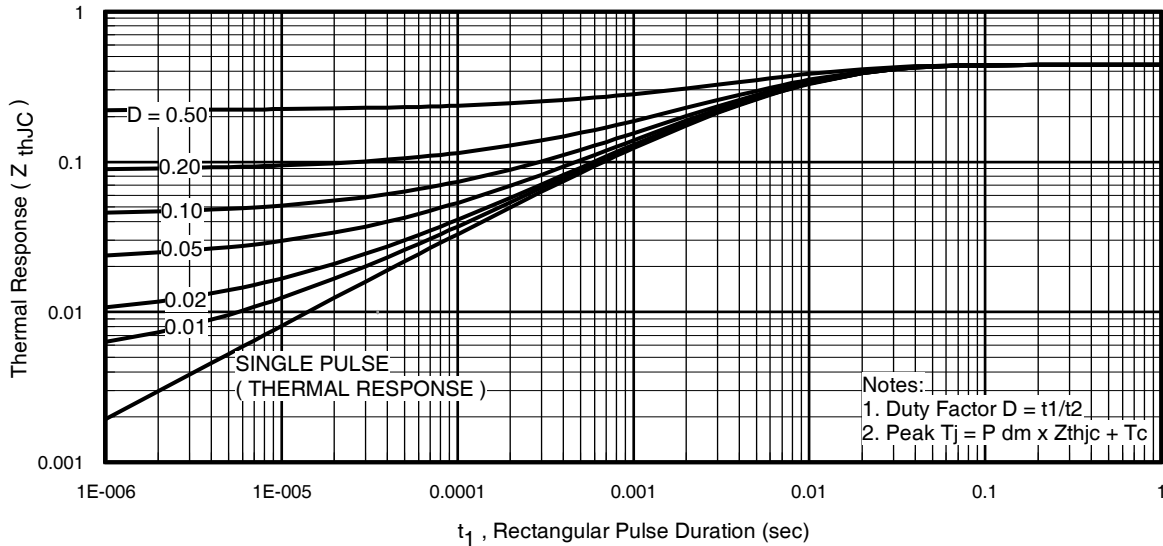


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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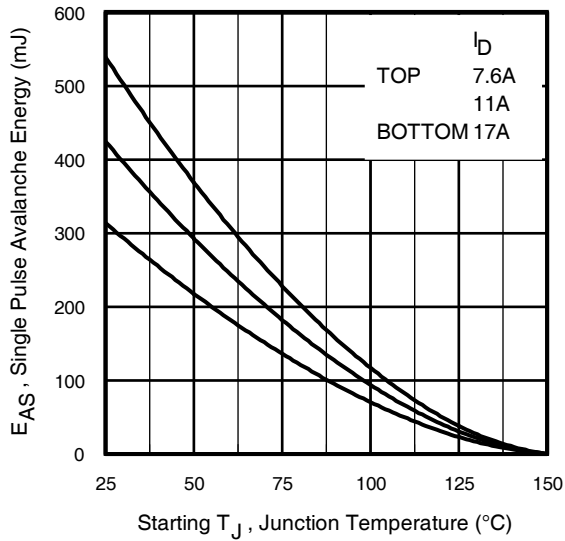


Fig 12. Maximum Avalanche Energy vs. Drain Current

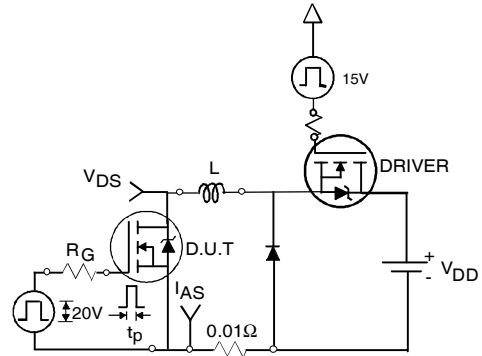


Fig 13a. Unclamped Inductive Test Circuit

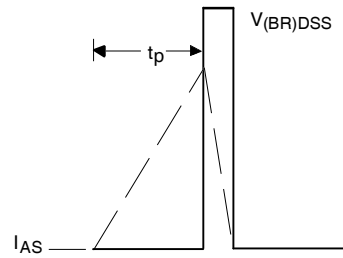


Fig 13b. Unclamped Inductive Waveforms

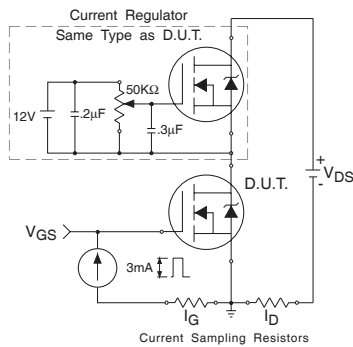


Fig 14a. Gate Charge Test Circuit

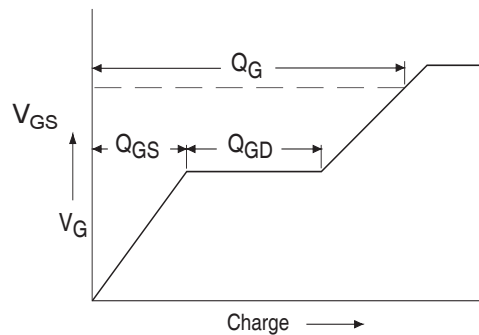
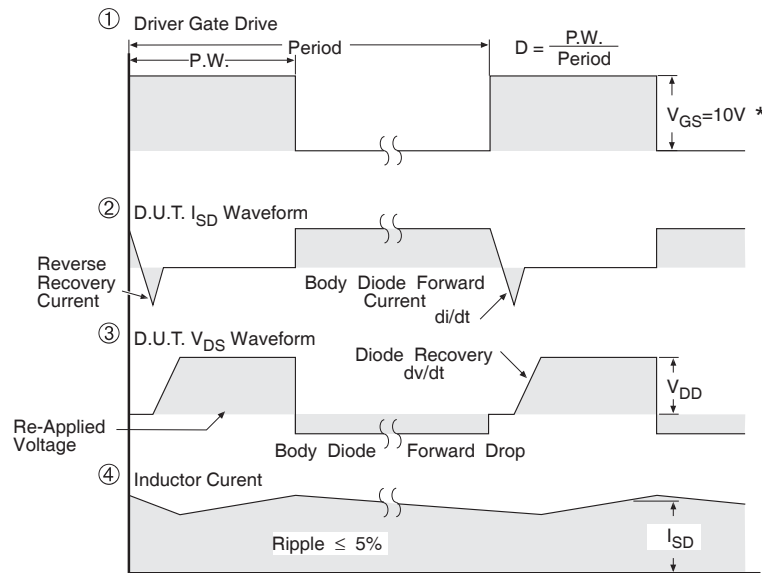
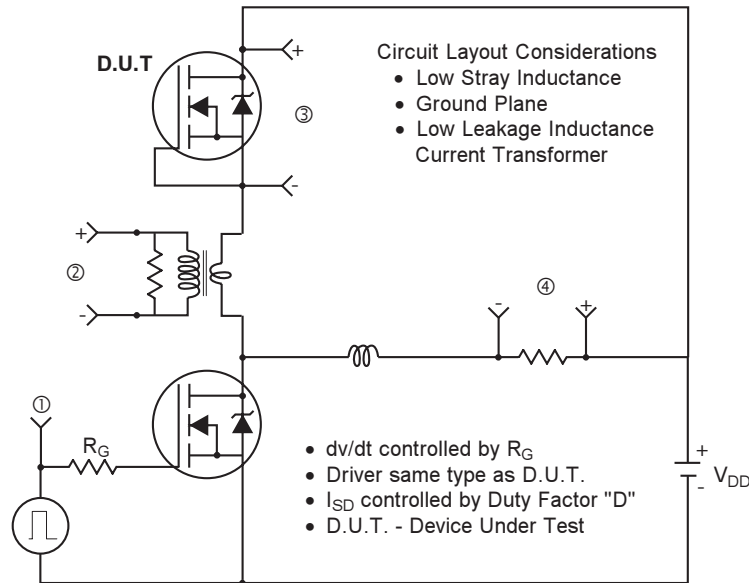


Fig 14b. Basic Gate Charge Waveform

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

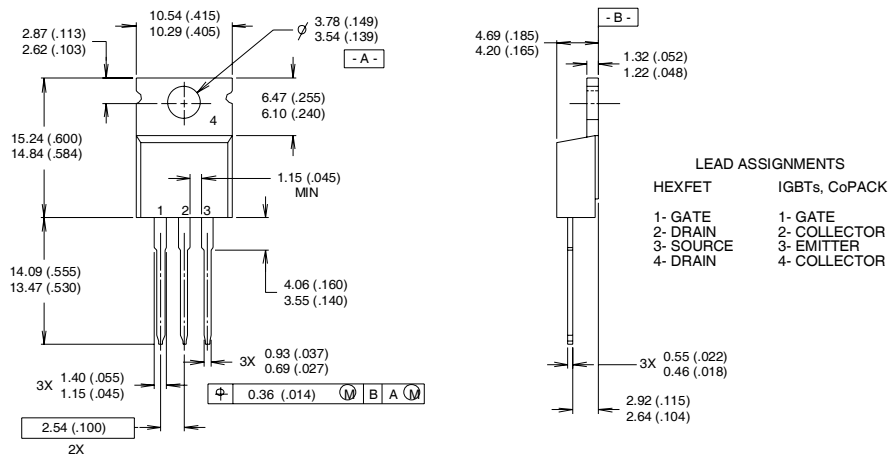
Fig 15. For N-Channel HEXFET® Power MOSFETs

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TO-220AB Package Outline

Dimensions are shown in millimeters (inches)

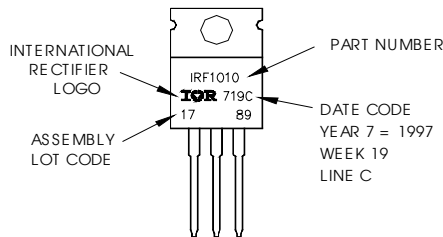


NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH
- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line
 position indicates "Lead-Free"



TO-220AB package is not recommended for Surface Mount Application.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.
 Qualification Standards can be found on IR's Web site.

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IR Rectifier

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